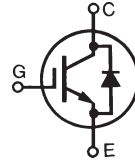


High Voltage BIMOSFET™ Monolithic Bipolar MOS Transistor Extended FBSOA

IXCH36N250 IXCK36N250



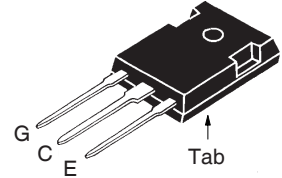
$$V_{CES} = 2500V$$

$$I_{C110} = 36A$$

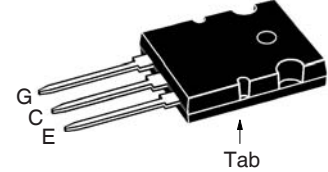
$$V_{CE(sat)} \leq 3.3V$$

Symbol	Test Conditions	Maximum Ratings	
V_{CES}	$T_C = 25^\circ C$ to $150^\circ C$	2500	V
V_{CGR}	$T_J = 25^\circ C$ to $150^\circ C$, $R_{GE} = 1M\Omega$	2500	V
V_{GES}	Continuous	± 25	V
V_{GEM}	Transient	± 35	V
I_{C25}	$T_C = 25^\circ C$	73	A
I_{C110}	$T_C = 110^\circ C$	36	A
I_{CM}	$T_C = 25^\circ C$, 1ms	360	A
SSOA (RBSOA)	$V_{GE} = 15V$, $T_{VJ} = 125^\circ C$, $R_G = 20\Omega$ Clamped Inductive Load	$I_{CM} = 144$ $V_{CE} \leq 0.8 \cdot V_{CES}$	A
T_{SC} (SCSOA)	$V_{GE} = 15V$, $T_J = 125^\circ C$, $R_G = 82\Omega$, $V_{CE} = 1250V$, Non-Repetitive	10	μs
P_C	$T_C = 25^\circ C$	595	W
T_J		-55 ... +150	$^\circ C$
T_{JM}		150	$^\circ C$
T_{stg}		-55 ... +150	$^\circ C$
T_L	1.6mm (0.062 in.) from Case for 10s	300	$^\circ C$
T_{SOLD}	Plastic Body for 10 seconds	260	$^\circ C$
M_d	Mounting Torque	1.13/10	Nm/lb.in.
Weight	TO-247	6	g
	TO-264	10	g

TO-247 AD



TO-264



G = Gate

C = Collector

E = Emitter

Tab = Collector

Features

- High Blocking Voltage
- High Peak Current Capability
- Anti-Parallel Diode
- Low Saturation Voltage
- Extended FBSOA and SCSOA

Advantages

- Low Gate Drive Requirement
- High Power Density

Applications

- Switch-Mode and Resonant-Mode Power Supplies
- Uninterruptible Power Supplies (UPS)
- Laser Generators
- Capacitor Discharge Circuits
- AC Switches
- Protection Circuits

Symbol	Test Conditions ($T_J = 25^\circ C$, Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ.	Max.
BV_{CES}	$I_C = 250\mu A$, $V_{GE} = 0V$	2500		V
$V_{GE(th)}$	$I_C = 250\mu A$, $V_{CE} = V_{GE}$	4.0		6.5 V
I_{CES}	$V_{CE} = V_{CES}$, $V_{GE} = 0V$ $T_J = 125^\circ C$			50 μA 1.75 mA
I_{GES}	$V_{CE} = 0V$, $V_{GE} = \pm 25V$			± 100 nA
$V_{CE(sat)}$	$I_C = 36A$, $V_{GE} = 15V$, Note 1 $T_J = 125^\circ C$	2.6 3.0		3.3 V V

Symbol Test Conditions

($T_J = 25^\circ\text{C}$ Unless Otherwise Specified)

Characteristic Values

Min. Typ. Max.

g_{fs}	$I_C = 36\text{A}, V_{CE} = 10\text{V}$, Note 1	22	33	S
C_{ies}	$V_{CE} = 25\text{V}, V_{GE} = 0\text{V}, f = 1\text{MHz}$		3980	pF
C_{oes}			170	pF
C_{res}			60	pF
Q_g	$I_C = 36\text{A}, V_{GE} = 15\text{V}, V_{CE} = 1000\text{V}$		177	nC
Q_{ge}			30	nC
Q_{gc}			80	nC
$t_{d(on)}$	Resistive Switching Times, $T_J = 25^\circ\text{C}$ $I_C = 36\text{A}, V_{GE} = 15\text{V}$ $V_{CE} = 1250\text{V}, R_G = 20\Omega$		115	ns
t_r			580	ns
$t_{d(off)}$			430	ns
t_f			880	ns
$t_{d(on)}$	Resistive Switching Times, $T_J = 125^\circ\text{C}$ $I_C = 36\text{A}, V_{GE} = 15\text{V}$ $V_{CE} = 1250\text{V}, R_G = 20\Omega$		105	ns
t_r			830	ns
$t_{d(off)}$			480	ns
t_f			900	ns
R_{thJC}				0.21 $^\circ\text{C/W}$
R_{thCS}	TO-247	0.21		$^\circ\text{C/W}$
	TO-264	0.15		$^\circ\text{C/W}$

Reverse Diode

Symbol Test Conditions

($T_J = 25^\circ\text{C}$ Unless Otherwise Specified)

Characteristic Values

Min. Typ. Max

V_F	$I_F = 36\text{A}, V_{GE} = 0\text{V}$, Note 1		2.5	V
t_{rr}	$I_F = 23\text{A}, V_{GE} = 0\text{V}, -di_F/dt = 100\text{A}/\mu\text{s}$		1.7	μs
I_{RM}			43	A

Note:

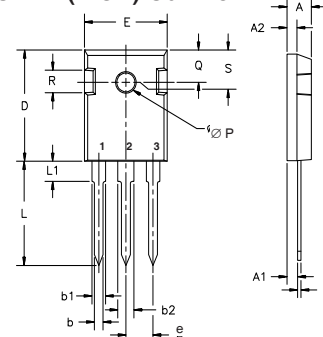
1. Pulse test, $t \leq 300\mu\text{s}$, duty cycle, $d \leq 2\%$.

Additional provisions for lead to lead voltage isolation are required at $V_{CE} > 1200\text{V}$.

IXYS Reserves the Right to Change Limits, Test Conditions and Dimensions.

IXYS MOSFETs and IGBTs are covered by one or more of the following U.S. patents:	4,835,592	4,931,844	5,049,961	5,237,481	6,162,665	6,404,065 B1	6,683,344	6,727,585	7,005,734 B2	7,157,338B2
	4,850,072	5,017,508	5,063,307	5,381,025	6,259,123 B1	6,534,343	6,710,405 B2	6,759,692	7,063,975 B2	
	4,881,106	5,034,796	5,187,117	5,486,715	6,306,728 B1	6,583,505	6,710,463	6,771,478 B2	7,071,537	

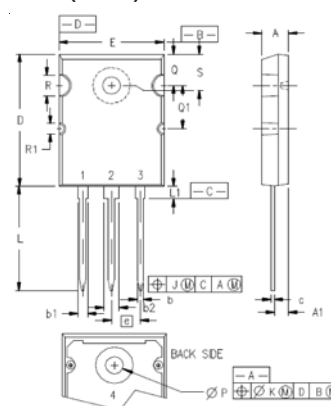
TO-247 (IXCH) Outline



Terminals: 1 - Gate 2 - Collector
3 - Emitter

Dim.	Millimeter Min.	Millimeter Max.	Inches Min.	Inches Max.
A	4.7	5.3	.185	.209
A ₁	2.2	2.54	.087	.102
A ₂	2.2	2.6	.059	.098
b	1.0	1.4	.040	.055
b ₁	1.65	2.13	.065	.084
b ₂	2.87	3.12	.113	.123
C	.4	.8	.016	.031
D	20.80	21.46	.819	.845
E	15.75	16.26	.610	.640
e	5.20	5.72	0.205	0.225
L	19.81	20.32	.780	.800
L1		4.50		.177
ØP	3.55	3.65	.140	.144
Q	5.89	6.40	0.232	0.252
R	4.32	5.49	.170	.216
S	6.15 BSC		.242 BSC	

TO-264 (IXCK) Outline



Terminals: 1 = Gate
2,4 = Collector
3 = Emitter

SYM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	.185	.209	4.70	5.31
A1	.102	.118	2.59	3.00
b	.037	.055	0.94	1.40
b1	.087	.102	2.21	2.59
b2	.110	.126	2.79	3.20
c	.017	.029	0.43	0.74
D	1.007	1.047	25.58	26.59
E	.760	.799	19.30	20.29
e		.215BSC		5.46 BSC
J	.000	.010	0.00	0.25
K	.000	.010	0.00	0.25
L	.779	.842	19.79	21.39
L1	.087	.102	2.21	2.59
ØP	.122	.136	3.10	3.51
Q	.240	.256	6.10	6.50
Q1	.330	.346	8.38	8.79
ØR	.155	.187	3.94	4.75
ØR1	.085	.093	2.16	2.36
S	.243	.253	6.17	6.43

Fig. 1. Output Characteristics @ $T_J = 25^\circ\text{C}$

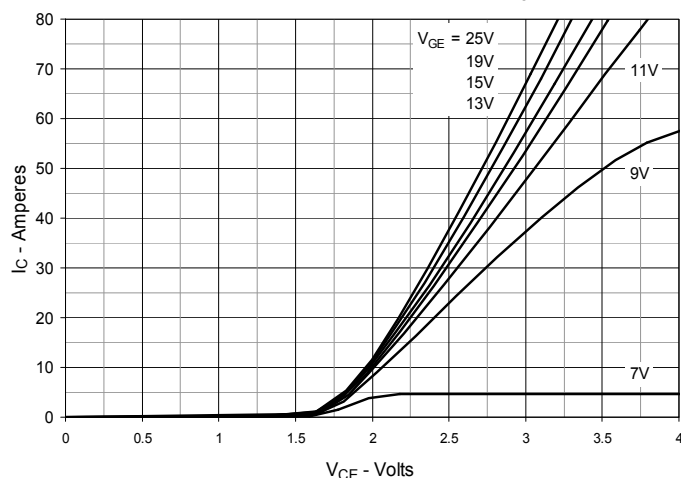


Fig. 2. Extended Output Characteristics @ $T_J = 25^\circ\text{C}$

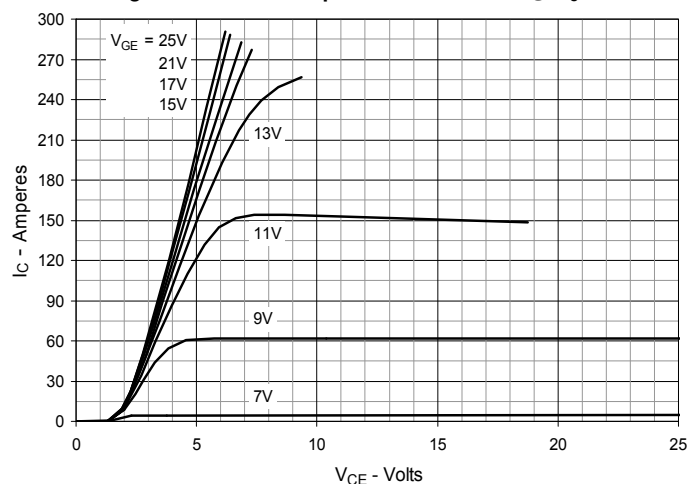


Fig. 3. Output Characteristics @ $T_J = 125^\circ\text{C}$

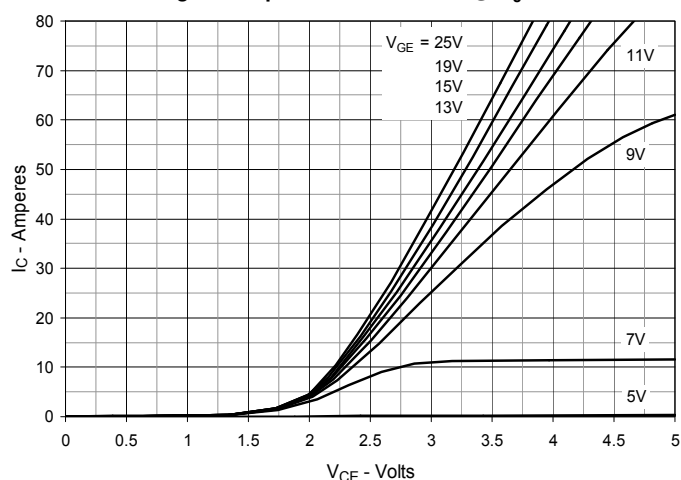


Fig. 4. Dependence of $V_{CE(sat)}$ on Junction Temperature

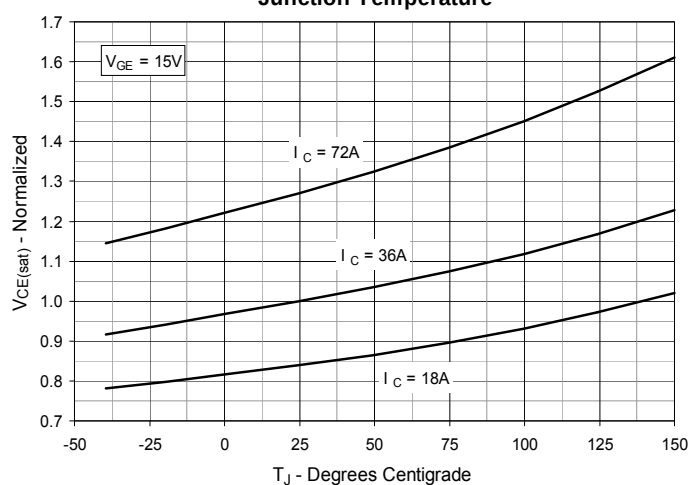


Fig. 5. Collector-to-Emitter Voltage vs. Gate-to-Emitter Voltage

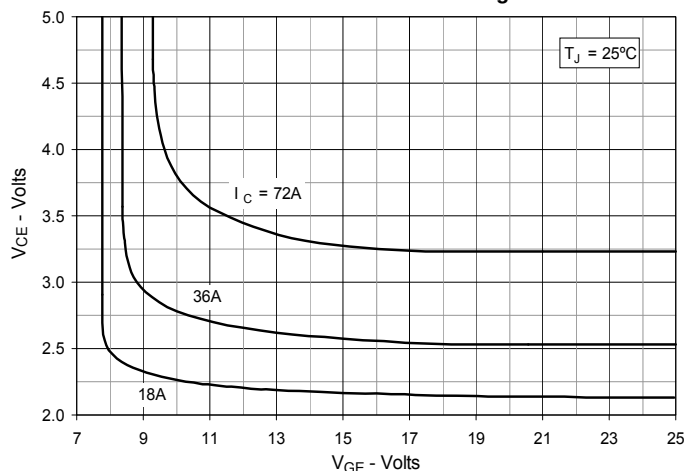


Fig. 6. Input Admittance

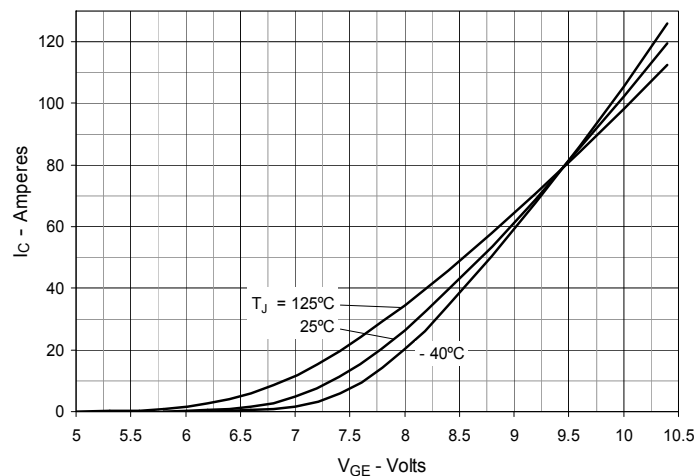


Fig. 7. Transconductance

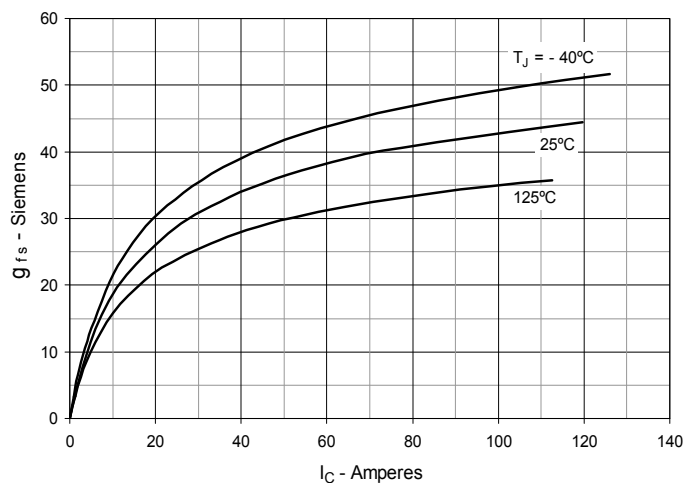


Fig. 8. Forward Voltage Drop of Intrinsic Diode

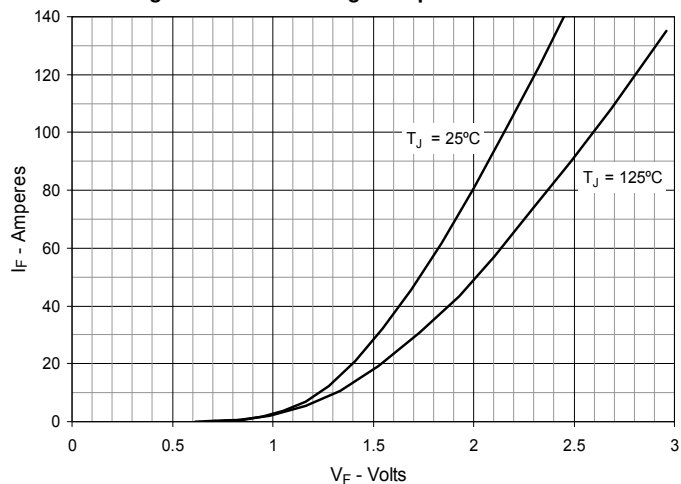


Fig. 9. Gate Charge

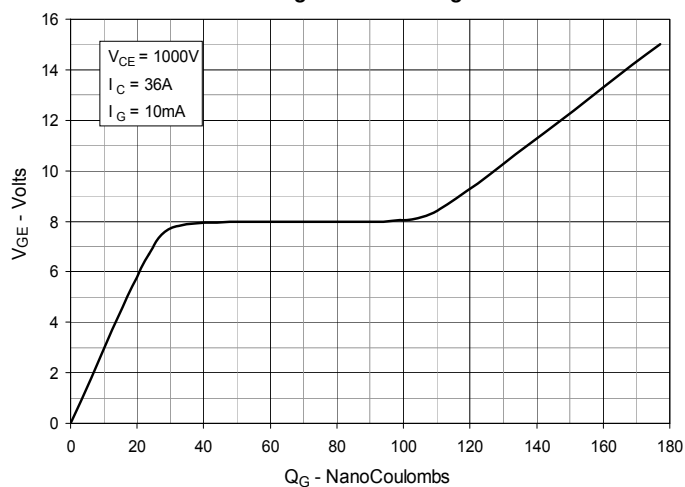


Fig. 10. Capacitance

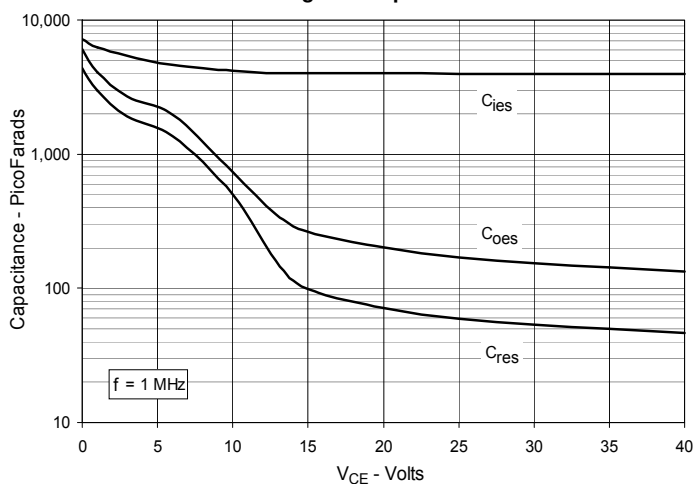


Fig. 11. Reverse-Bias Safe Operating Area

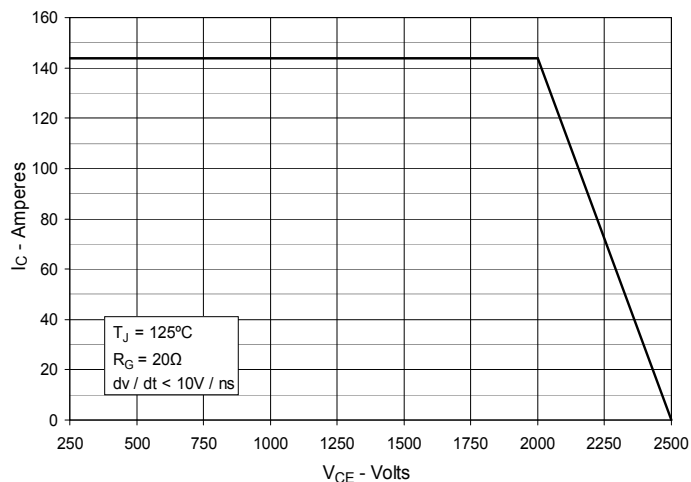


Fig. 12. Maximum Transient Thermal Impedance

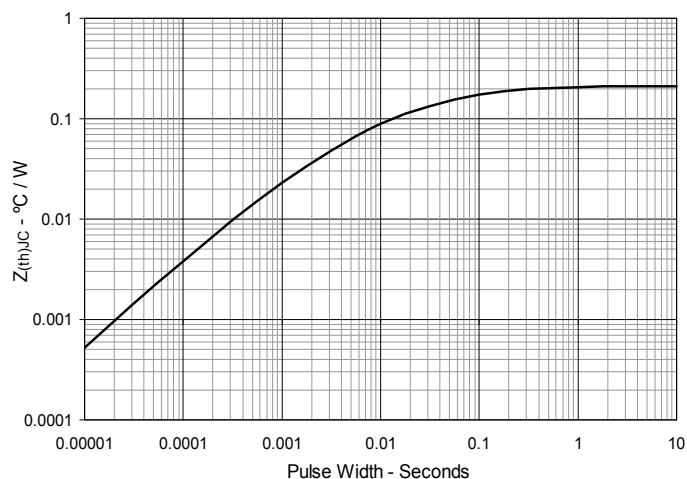


Fig. 13. Forward-Bias Safe Operating Area @ $T_C = 25^\circ\text{C}$

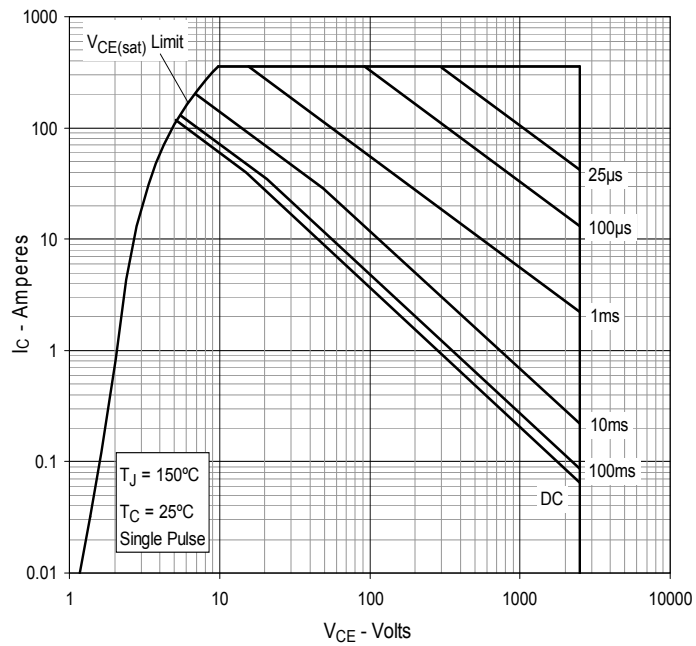
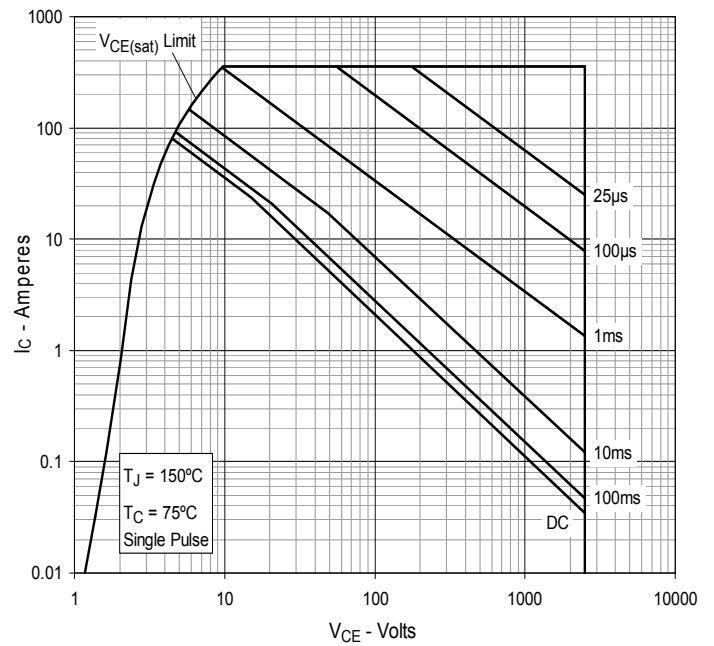


Fig. 14. Forward-Bias Safe Operating Area @ $T_C = 75^\circ\text{C}$





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